



#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

BV <sub>DSS</sub>	Max R <sub>DS(ON)</sub>	Max I <sub>D</sub> T <sub>A</sub> = +25°C (Note 3)
60V	40mΩ @ V <sub>GS</sub> = 10V	7.7A
00 V	60mΩ @ V <sub>GS</sub> = 4.5V	6.3A

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- · Disconnect Switches
- Motor Control

## **Features and Benefits**

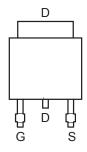
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

#### **Mechanical Data**

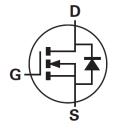
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- · Weight: 0.33 grams (approximate)







Pin Out -Top View



**Equivalent Circuit** 

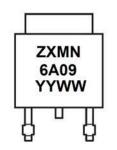
#### Ordering Information (Note 4 & 5)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A09KQTC	ZXMN6A09	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZXMN6A09 = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 10 = 2010) WW = Week (01 - 53)



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current		(Note 7)	ID	11.8	
	V <sub>GS</sub> = 10V	T <sub>A</sub> = +70°C (Note 7)		9.6	Α
		(Note 6)		7.7	
Pulsed Drain Current (Note 8)		I <sub>DM</sub>	43	А	
Continuous Source Current (Body Diode) (Note 7)		Is	10.8	A	
Pulsed Source Current (Body Diode) (Note 8)		I <sub>SM</sub>	43	А	

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		4.3 34.4	
Power Dissipation Linear Derating Factor	(Note 7)	P <sub>D</sub>	10.1 80.8	W mW/°C
	(Note 9)		2.15 17.2	
	(Note 6)		29	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	12.3	0000
	(Note 9)		58.1	°C/W
Thermal Resistance, Junction to Lead	(Note 10)	$R_{\theta JL}$	1.04	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

Notes:

- 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

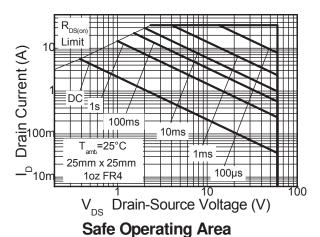
  7. For a device surface mounted on FR4 PCB measured at t ≤ 10 sec.

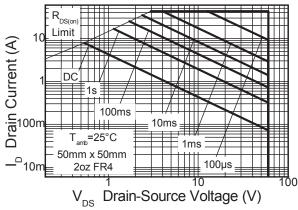
  8. Repetitive rating 50mm x 1.6mm FR4 PCB, D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction
- temperature.
- 9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

  10. Thermal resistance from junction to solder-point (at the end of the drain lead).

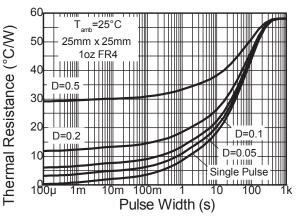


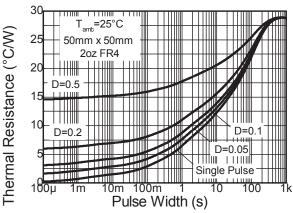
#### **Thermal Characteristics**





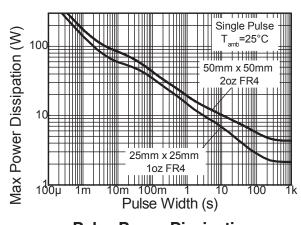
**Safe Operating Area** 

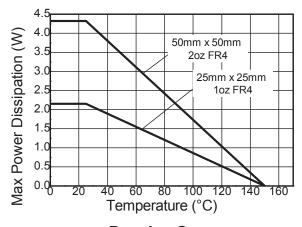




**Transient Thermal Impedance** 

**Transient Thermal Impedance** 





**Pulse Power Dissipation** 

**Derating Curve** 



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

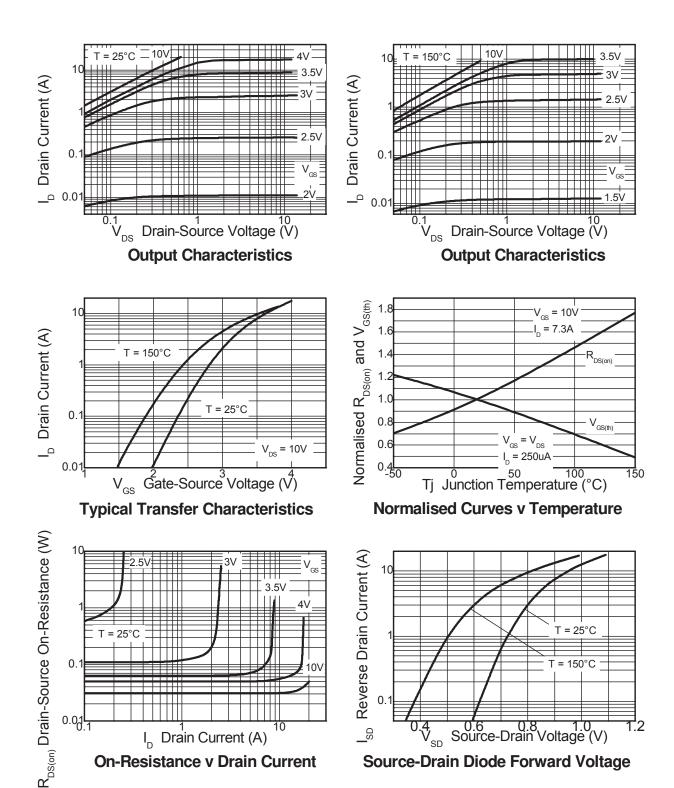
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	1.0		3.0	٧	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 11)	D			40	m0	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.3A	
Static Dialii-Source Off-Resistance (Note 11)	R <sub>DS(ON)</sub>	_	_	60	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.6A	
Forward Transconductance (Notes 11 & 12)	g <sub>fs</sub>	_	15	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 7.3A	
Diode Forward Voltage (Note 11)	$V_{SD}$	_	0.85	0.95	V	I <sub>S</sub> = 6.6A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
Reverse recovery time (Note 12)	t <sub>rr</sub>	_	25.6	_	ns	I <sub>S</sub> = 3A, di/dt = 100A/μs	
Reverse recovery charge (Note 12)	$Q_{rr}$	_	26.0	_	nC	T <sub>J</sub> = +25°C	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	C <sub>iss</sub>	_	1426	-	pF		
Output Capacitance	Coss	_	134	_	pF	$V_{DS} = 30V$ , $V_{GS} = 0V$ - $f = 1MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	64	1	pF		
Total Gate Charge (Note 13)	$Q_g$	_	15	_	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 30V, I <sub>D</sub> = 5.6A	
Total Gate Charge (Note 13)	Qg	_	29	_	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V -I <sub>D</sub> = 7.3A	
Gate-Source Charge (Note 13)	Q <sub>gs</sub>	_	7.0	_	nC		
Gate-Drain Charge (Note 13)	$Q_{gd}$	_	4.7	_	nC		
Turn-On Delay Time (Note 13)	t <sub>D(on)</sub>	_	4.8	_	ns		
Turn-On Rise Time (Note 13)	t <sub>r</sub>	_	4.6	_	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V	
Turn-Off Delay Time (Note 13)	t <sub>D(off)</sub>	_	32.5	_	ns	$I_D$ = 1A, $R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 13)	t <sub>f</sub>	_	14.5	_	ns		

Notes:

- 11. Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2% 12. For design aid only, not subject to production testing. 13. Switching characteristics are independent of operating junction temperatures.

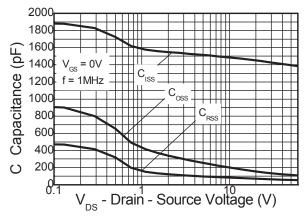


## **Typical Characteristics**

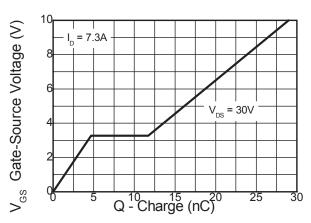




#### **Typical Characteristics** (cont.)

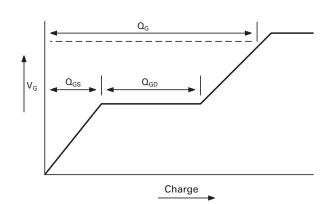


Capacitance v Drain-Source Voltage

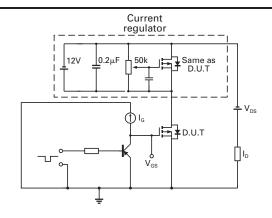


Gate-Source Voltage v Gate Charge

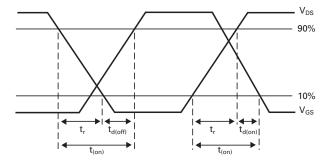
# **Test Circuits**



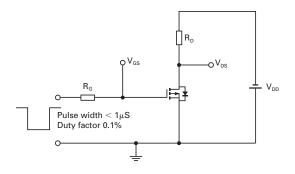
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

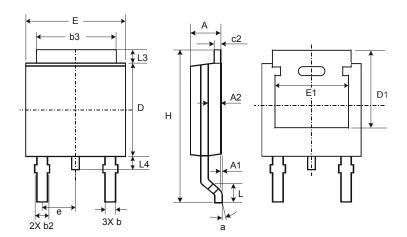


Switching time test circuit



# **Package Outline Dimensions**

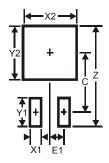
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	_	-		
е	_	_	2.286		
Е	6.45	6.70	6.58		
E1	4.32	_	_		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	_		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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